LM5109 100V/1A Peak Half Bridge Gate Driver

Check for Samples: LM5109

FEATURES

- **Drives Both a High Side and Low Side N-Channel MOSFET**
- **1A Peak Output Current (1.0A Sink / 1.0A Source)**
- **Independent TTL Compatible Inputs**
- **Bootstrap Supply Voltage to 118V DC**
- **Fast Propagation Times (27 ns Typical)**
- **Drives 1000 pF Load with 15ns Rise and Fall Times**
- **Excellent Propagation Delay Matching (2 ns Typical)**
- **Supply Rail Under-voltage Lockout**
- **Low Power Consumption**
- **Pin Compatible with ISL6700**

TYPICAL APPLICATIONS

- **Current Fed Push-pull Converters**
- **Half and Full Bridge Power Converters**
- **Solid State Motor Drives**
- **Two Switch Forward Power Converters**

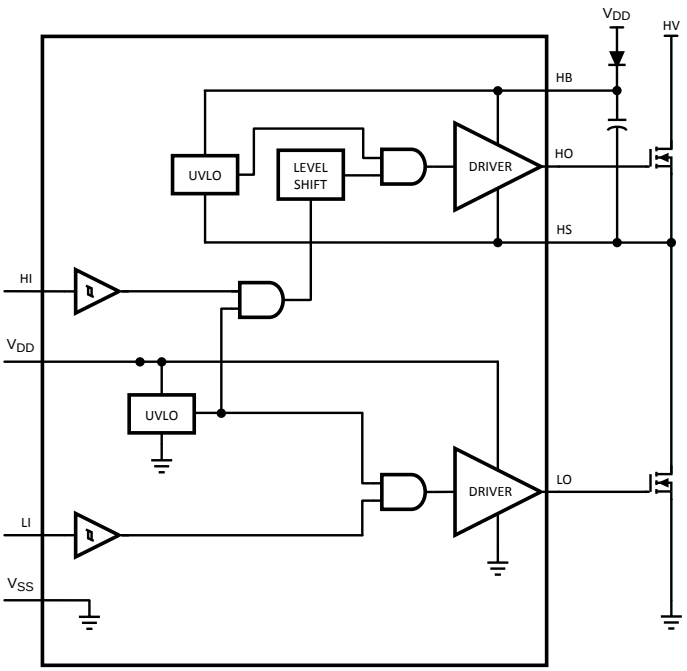
PACKAGE

- **SOIC-8**
- **WSON-8 (4 mm x 4 mm)**

DESCRIPTION

The LM5109 is a low cost high voltage gate driver, designed to drive both the high side and the low side N-Channel MOSFETs in a synchronous buck or a half bridge configuration. The floating high-side driver is capable of working with rail voltages up to 100V. The outputs are independently controlled with TTL compatible input thresholds. A robust level shifter technology operates at high speed while consuming low power and providing clean level transitions from the control input logic to the high side gate driver. Under-voltage lockout is provided on both the low side and the high side power rails. The device is available in the SOIC-8 and the thermally enhanced WSON-8 packages.

SIMPLIFIED BLOCK DIAGRAM



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

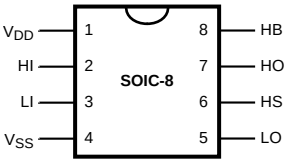
All trademarks are the property of their respective owners.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

Copyright © 2005, Texas Instruments Incorporated

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

CONNECTION DIAGRAMS



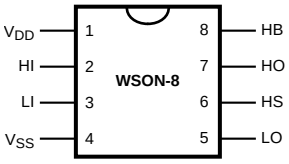


Figure 1.

Table 1. PIN DESCRIPTION

Pin No.		Name	Description	Application Information
SO-8	WSON-8 (1)			
1	1	V_{DD}	Positive gate drive supply	Locally decouple to V_{SS} using low ESR/ESL capacitor located as close to IC as possible.
2	2	HI	High side control input	The LM5109 HI input is compatible with TTL input thresholds. Unused HI input should be tied to ground and not left open
3	3	LI	Low side control input	The LM5109 LI input is compatible with TTL input thresholds. Unused LI input should be tied to ground and not left open.
4	4	V_{SS}	Ground reference	All signals are referenced to this ground.
5	5	LO	Low side gate driver output	Connect to the gate of the low side N-MOS device.
6	6	HS	High side source connection	Connect to the negative terminal of the bootstrap capacitor and to the source of the high side N-MOS device.
7	7	HO	High side gate driver output	Connect to the gate of the low side N-MOS device.
8	8	HB	High side gate driver positive supply rail	Connect the positive terminal of the bootstrap capacitor to HB and the negative terminal of the bootstrap capacitor to HS. The bootstrap capacitor should be placed as close to IC as possible.

(1) **For WSON-8 package it is recommended that the exposed pad on the bottom of the LM5109 be soldered to ground plane on the PCB board and the ground plane should extend out from underneath the package to improve heat dissipation.**

Copyright © 2005, Texas Instruments Incorporated

ABSOLUTE MAXIMUM RATINGS (1)

If Military/Aerospace specified devices are required, contact the Texas Instruments Sales Office/Distributors for availability and specifications.

V_{DD} to V_{SS}	-0.3V to 18V
HB to HS	−0.3V to 18V
LI or HI to V_{SS}	−0.3V to V_{DD} +0.3V
LO to V_{SS}	−0.3V to V_{DD} +0.3V
HO to V_{SS}	V_{HS} −0.3V to V_{HB} +0.3V
HS to V_{SS} (2)	−5V to 100V
HB to V_{SS}	118V
Junction Temperature	-40°C to +150°C
Storage Temperature Range	−55°C to +150°C
ESD Rating HBM (3)	2 kV

(1) Absolute Maximum Ratings indicate limits beyond which damage to the component may occur. Operating Ratings are conditions under which operation of the device is specified. Operating Ratings **do not** imply specified performance limits. For specified performance limits and associated test conditions, see the Electrical Characteristics tables.

(2) In the application the HS node is clamped by the body diode of the external lower N-MOSFET, therefore the HS voltage will generally not exceed -1V. However in some applications, board resistance and inductance may result in the HS node exceeding this stated voltage transiently. If negative transients occur on HS, the HS voltage must never be more negative than V_{DD} - 15V. For example, if V_{DD} = 10V, the negative transients at HS must not exceed -5V.

(3) The human body model is a 100 pF capacitor discharged through a 1.5kΩ resistor into each pin. Pin 6 , Pin 7 and Pin 8 are rated at 500V.

RECOMMENDED OPERATING CONDITIONS

V_{DD}	8V to 14V
HS (1)	−1V to 100V
HB	V_{HS} +8V to V_{HS} +14V
HS Slew Rate	< 50 V/ns
Junction Temperature	−40°C to +125°C

(1) In the application the HS node is clamped by the body diode of the external lower N-MOSFET, therefore the HS voltage will generally not exceed -1V. However in some applications, board resistance and inductance may result in the HS node exceeding this stated voltage transiently. If negative transients occur on HS, the HS voltage must never be more negative than V_{DD} - 15V. For example, if V_{DD} = 10V, the negative transients at HS must not exceed -5V.

ELECTRICAL CHARACTERISTICS

Specifications in standard typeface are for T_J = +25°C, and those in **boldface type** apply over the full **operating junction temperature range**. Unless otherwise specified, V_{DD} = V_{HB} = 12V, V_{SS} = V_{HS} = 0V, No Load on LO or HO.

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Units
SUPPLY CURRENTS						
I_{DD}	V_{DD} Quiescent Current	LI = HI = 0V		0.3	**0.6**	mA
I_{DDO}	V_{DD} Operating Current	f = 500 kHz		2.1	**3.4**	mA
I_{HB}	Total HB Quiescent Current	LI = HI = 0V		0.06	**0.2**	mA
I_{HBO}	Total HB Operating Current	f = 500 kHz		1.6	**3.0**	mA
I_{HBS}	HB to V_{SS} Current, Quiescent	V_{HS} = V_{HB} = 100V		0.1	**10**	µA
I_{HBSO}	HB to V_{SS} Current, Operating	f = 500 kHz		0.5		mA
INPUT PINS LI and HI						
V_{IL}	Low Level Input Voltage Threshold		**0.8**	1.8		V
V_{IH}	High Level Input Voltage Threshold			1.8	**2.2**	V
R_I	Input Pulldown Resistance		**100**	180	**500**	kΩ
UNDER VOLTAGE PROTECTION						
V_{DDR}	V_{DD} Rising Threshold	V_{DDR} = V_{DD} - V_{SS}	**6.0**	6.9	**7.4**	V

(1) Min and Max limits are 100% production tested at 25°C. Limits over the operating temperature range are specified through correlation using Statistical Quality Control (SQC) methods. Limits are used to calculate Texas Instrument's Average Outgoing Quality Level (AOQL).

Copyright © 2005, Texas Instruments Incorporated

ELECTRICAL CHARACTERISTICS (continued)

Specifications in standard typeface are for T_J = +25°C, and those in **boldface type** apply over the full **operating junction temperature range**. Unless otherwise specified, V_{DD} = V_{HB} = 12V, V_{SS} = V_{HS} = 0V, No Load on LO or HO.

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Units
V_{DDH}	V_{DD} Threshold Hysteresis			0.5		V
V_{HBR}	HB Rising Threshold	V_{HBR} = V_{HB} - V_{HS}	**5.7**	6.6	**7.1**	V
V_{HBH}	HB Threshold Hysteresis			0.4		V
LO GATE DRIVER						
V_{OLL}	Low-Level Output Voltage	I_{LO} = 100 mA, V_{OHL} = V_{LO} – V_{SS}		0.28	**0.45**	V
V_{OHL}	High-Level Output Voltage	I_{LO} = −100 mA, V_{OHL} = V_{DD}– V_{LO}		0.45	**0.75**	V
I_{OHL}	Peak Pullup Current	V_{LO} = 0V		1.0		A
I_{OLL}	Peak Pulldown Current	V_{LO} = 12V		1.0		A
HO GATE DRIVER						
V_{OLH}	Low-Level Output Voltage	I_{HO} = 100 mA, V_{OLH} = V_{HO}– V_{HS}		0.28	**0.45**	V
V_{OHH}	High-Level Output Voltage	I_{HO} = −100 mA, V_{OHH} = V_{HB}– V_{HO}		0.45	**0.75**	V
I_{OHH}	Peak Pullup Current	V_{HO} = 0V		1.0		A
I_{OLH}	Peak Pulldown Current	V_{HO} = 12V		1.0		A
THERMAL RESISTANCE						
θ_{JA}(2)	Junction to Ambient	SOIC-8		160		°C/W
		WSON-8 (3)		40		

(2) The θ_{JA} is not a constant for the package and depends on the printed circuit board design and the operating conditions.
(3) 4 layer board with Cu finished thickness 1.5/1/1/1.5 oz. Maximum die size used. 5x body length of Cu trace on PCB top. 50 x 50mm ground and power planes embedded in PCB. See Application Note AN-1187 (SNOA401).

SWITCHING CHARACTERISTICS

Specifications in standard typeface are for T_J = +25°C, and those in **boldface type** apply over the full **operating junction temperature range**. Unless otherwise specified, V_{DD} = V_{HB} = 12V, V_{SS} = V_{HS} = 0V, No Load on LO or HO.

Symbol	Parameter	Conditions	Min	Typ	Max	Units
LM5109						
t_{LPHL}	Lower Turn-Off Propagation Delay (LI Falling to LO Falling)			27	**56**	ns
t_{HPHL}	Upper Turn-Off Propagation Delay (HI Falling to HO Falling)			27	**56**	ns
t_{LPLH}	Lower Turn-On Propagation Delay (LI Rising to LO Rising)			29	**56**	ns
t_{HPLH}	Upper Turn-On Propagation Delay (HI Rising to HO Rising)			29	**56**	ns
t_{MON}	Delay Matching: Lower Turn-On and Upper Turn-Off			2	**15**	ns
t_{MOFF}	Delay Matching: Lower Turn-Off and Upper Turn-On			2	**15**	ns
t_{RC}, t_{FC}	Either Output Rise/Fall Time	C_L = 1000 pF		15	-	ns
t_{PW}	Minimum Input Pulse Width that Changes the Output			50		ns

Copyright © 2005, Texas Instruments Incorporated

TYPICAL PERFORMANCE CHARACTERISTICS

V_{DD} Operating Current vs Frequency

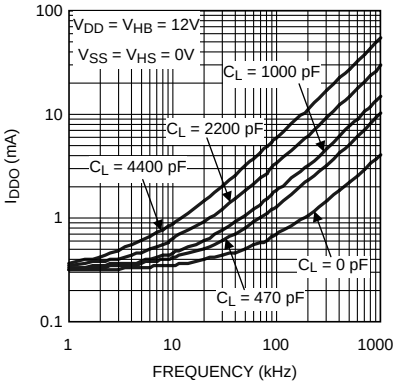


Figure 2.

HB Operating Current vs Frequency

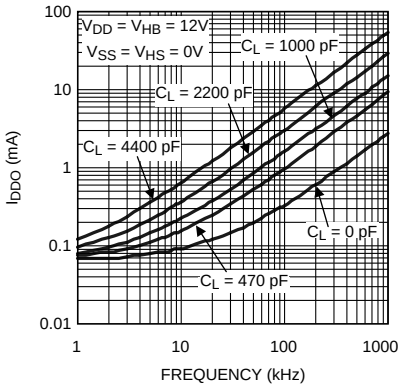


Figure 3.

Operating Current vs Temperature

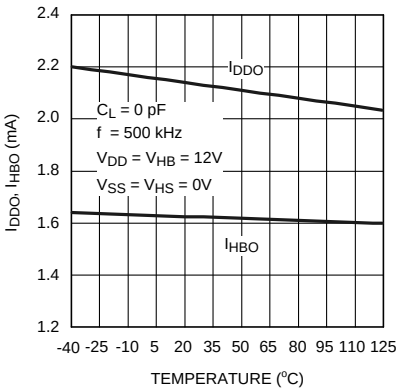


Figure 4.

Quiescent Current vs Temperature

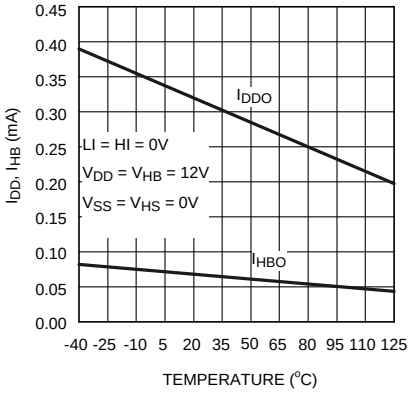


Figure 5.

Quiescent Current vs Voltage

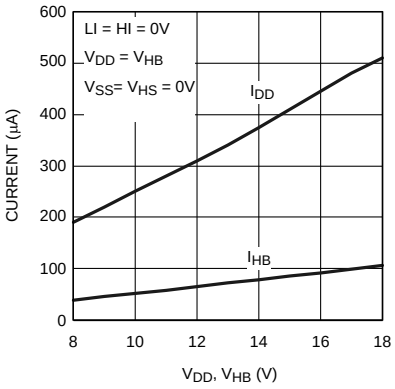


Figure 6.

Propagation Delay vs Temperature

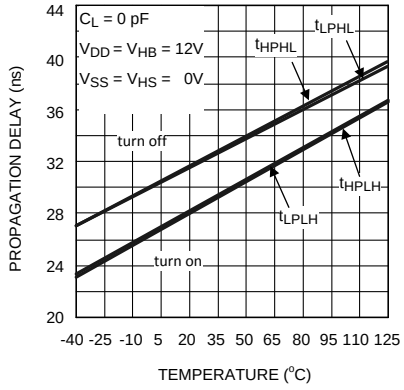


Figure 7.

Copyright © 2005, Texas Instruments Incorporated

TYPICAL PERFORMANCE CHARACTERISTICS (continued)

LO and HO High Level Output Voltage vs Temperature

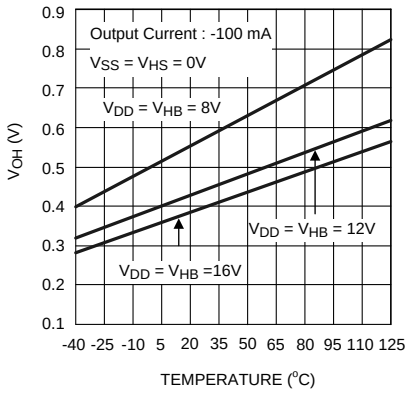


Figure 8.

LO and HO Low Level Output Voltage vs Temperature

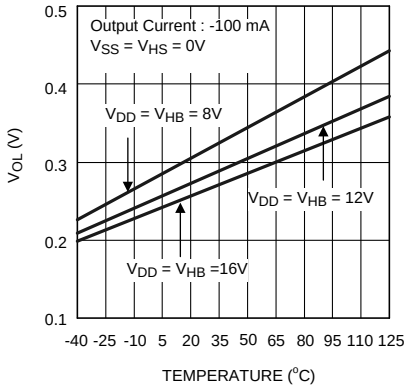


Figure 9.

Undervoltage Rising Thresholds vs Temperature

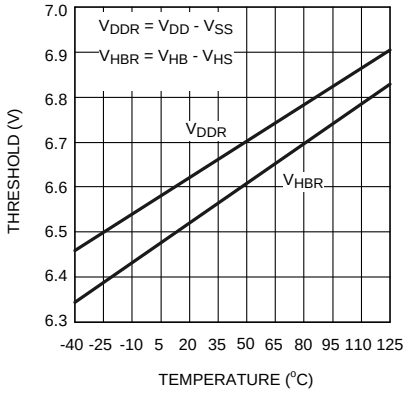


Figure 10.

Undervoltage Hysteresis vs Temperature

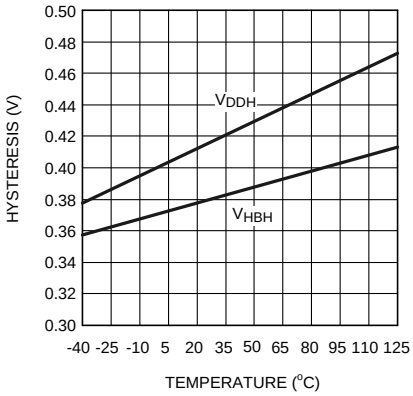


Figure 11.

Input Thresholds vs Temperature

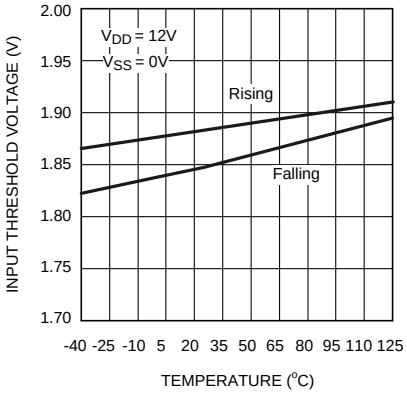


Figure 12.

Input Thresholds vs Supply Voltage

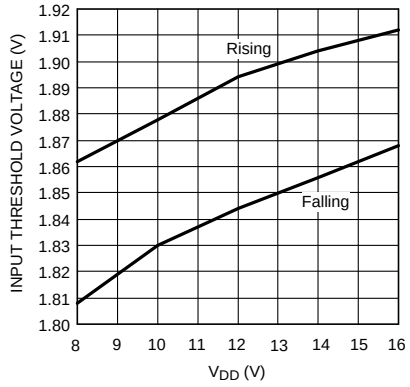
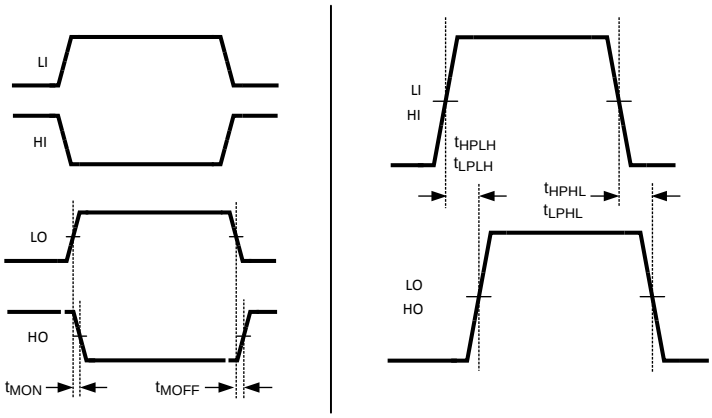


Figure 13.

Copyright © 2005, Texas Instruments Incorporated

TIMING DIAGRAM



LAYOUT CONSIDERATIONS

The optimum performance of high and low side gate drivers cannot be achieved without taking due considerations during circuit board layout. Following points are emphasized.

1. A low ESR / ESL capacitor must be connected close to the IC, and between V_{DD} and V_{SS} pins and between HB and HS pins to support high peak currents being drawn from VDD during turn-on of the external MOSFET.
2. To prevent large voltage transients at the drain of the top MOSFET, a low ESR electrolytic capacitor must be connected between MOSFET drain and ground (V_{SS}).
3. In order to avoid large negative transients on the switch node (HS) pin, the parasitic inductances in the source of top MOSFET and in the drain of the bottom MOSFET (synchronous rectifier) must be minimized.
4. Grounding Considerations:
   (a) The first priority in designing grounding connections is to confine the high peak currents from charging and discharging the MOSFET gate in a minimal physical area. This will decrease the loop inductance and minimize noise issues on the gate terminal of the MOSFET. The MOSFETs should be placed as close as possible to the gate driver.
   (b) The second high current path includes the bootstrap capacitor, the bootstrap diode, the local ground referenced bypass capacitor and low side MOSFET body diode. The bootstrap capacitor is recharged on the cycle-by-cycle basis through the bootstrap diode from the ground referenced V_{DD} bypass capacitor. The recharging occurs in a short time interval and involves high peak current. Minimizing this loop length and area on the circuit board is important to ensure reliable operation.

HS TRANSIENT VOLTAGES BELOW GROUND

The HS node will always be clamped by the body diode of the lower external FET. In some situations, board resistances and inductances can cause the HS node to transiently swing several volts below ground. The HS node can swing below ground provided:

1. HS must always be at a lower potential than HO. Pulling HO more than -0.3V below HS can activate parasitic transistors resulting in excessive current to flow from the HB supply possibly resulting in damage to the IC. The same relationship is true with LO and VSS. If necessary, a Schottky diode can be placed externally between HO and HS or LO and GND to protect the IC from this type of transient. The diode must be placed as close to the IC pins as possible in order to be effective.
2. HB to HS operating voltage should be 15V or less. Hence, if the HS pin transient voltage is -5V, VDD should be ideally limited to 10V to keep HB to HS below 15V.
3. A low ESR bypass capacitor between HB to HS as well as VDD to VSS is essential for proper operation. The capacitor should be located at the leads of the IC to minimize series inductance. The peak currents from LO and HO can be quite large. Any series inductances with the bypass capacitor will cause voltage ringing at the leads of the IC which must be avoided for reliable operation.

Copyright © 2005, Texas Instruments Incorporated

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
LM5109MA/NOPB	Active	Production	SOIC (D) | 8	95 | TUBE	Yes	NIPDAU | SN	Level-1-260C-UNLIM	-	L5109 MA
LM5109MA/NOPB.A	Active	Production	SOIC (D) | 8	95 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	See LM5109MA/NOPB	L5109 MA
LM5109MA/NOPB.B	Active	Production	SOIC (D) | 8	95 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	See LM5109MA/NOPB	L5109 MA
LM5109MAX/NOPB	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	NIPDAU | SN	Level-1-260C-UNLIM	-	L5109 MA
LM5109MAX/NOPB.A	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	See LM5109MAX/ NOPB	L5109 MA
LM5109MAX/NOPB.B	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	See LM5109MAX/ NOPB	L5109 MA

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

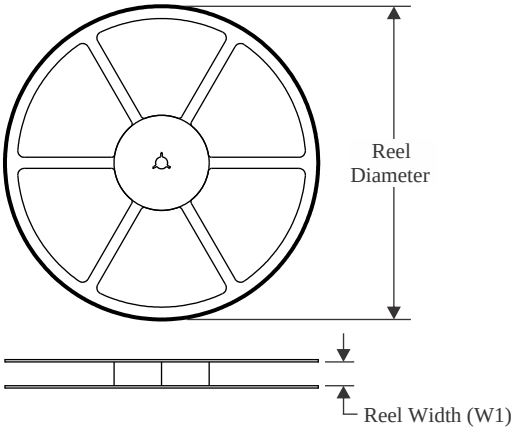
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

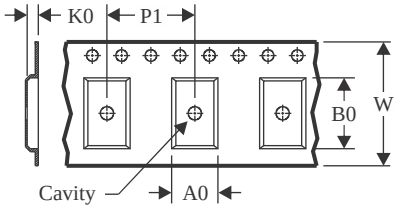
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

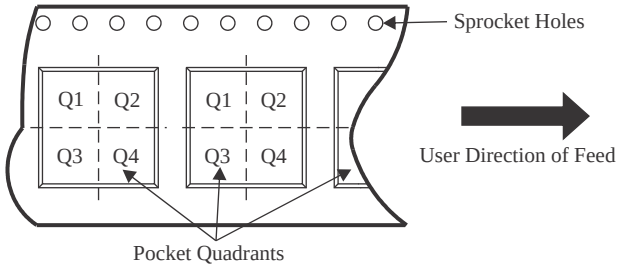


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

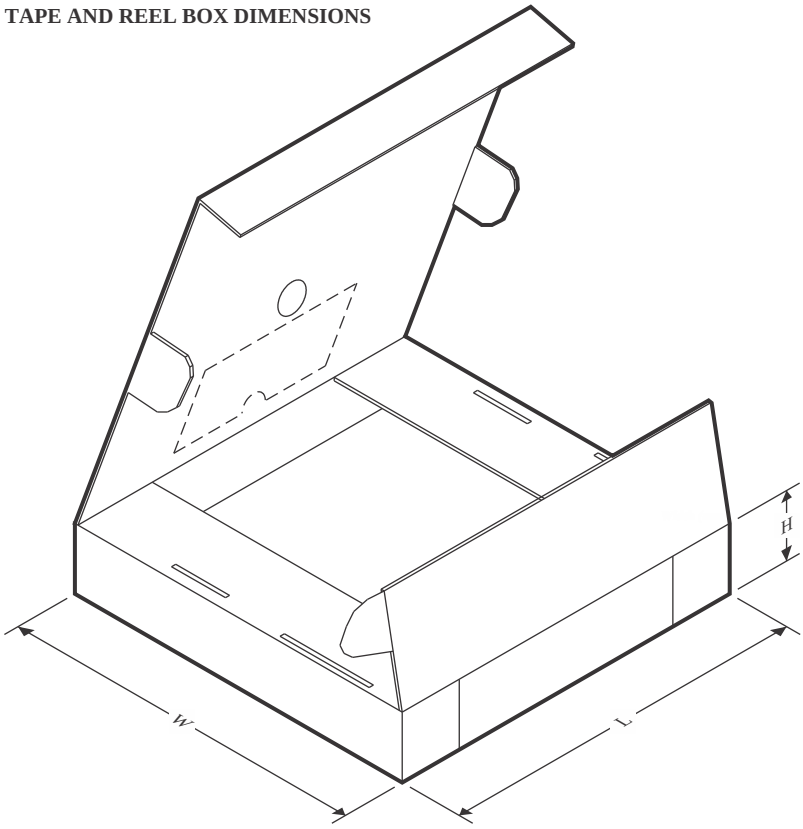
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LM5109MAX/NOPB	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

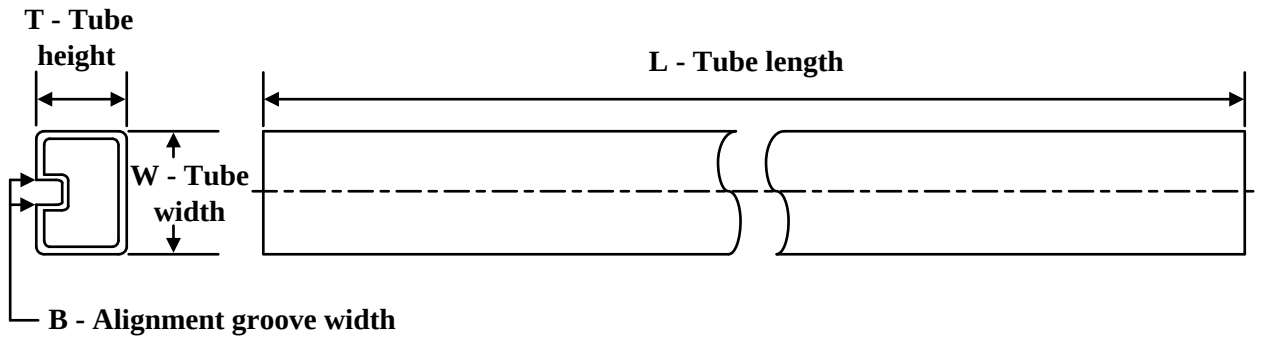
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

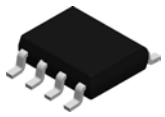
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LM5109MAX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
LM5109MA/NOPB	D	SOIC	8	95	495	8	4064	3.05
LM5109MA/NOPB.A	D	SOIC	8	95	495	8	4064	3.05
LM5109MA/NOPB.B	D	SOIC	8	95	495	8	4064	3.05

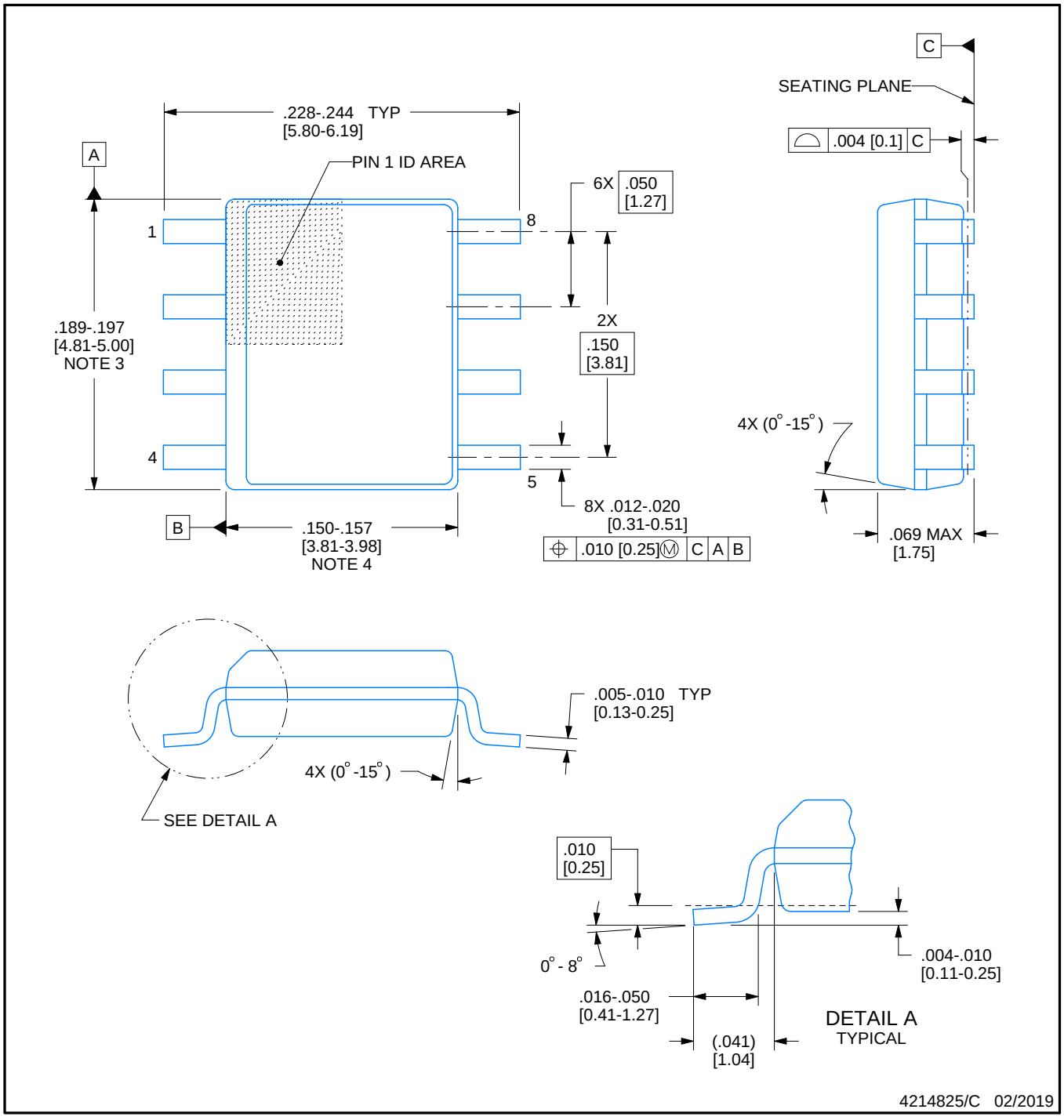


PACKAGE OUTLINE

D0008A

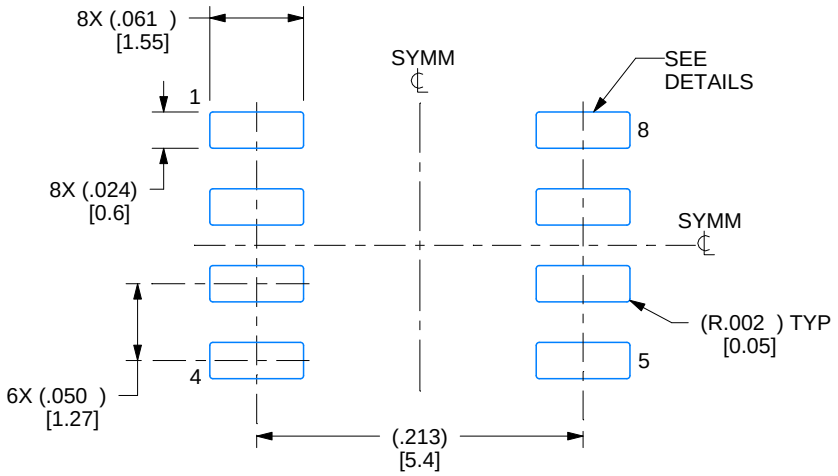
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

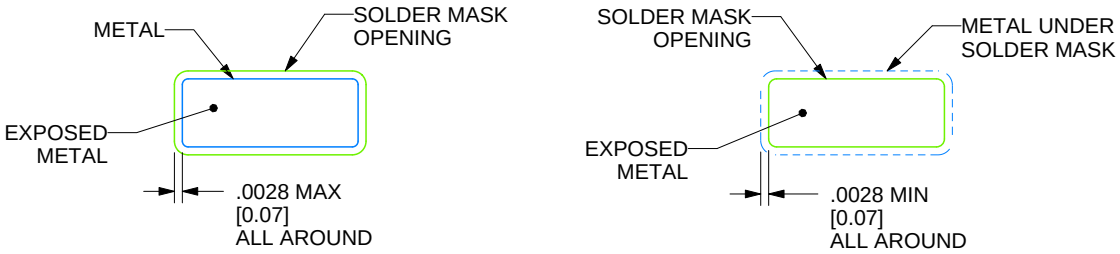


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

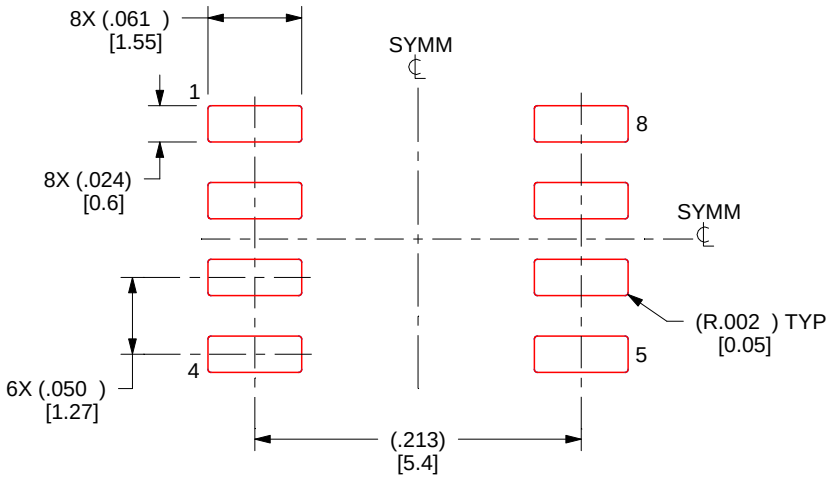
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES “AS IS” AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you fully indemnify TI and its representatives against any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI’s products are provided subject to TI’s Terms of Sale, TI’s General Quality Guidelines, or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI’s provision of these resources does not expand or otherwise alter TI’s applicable warranties or warranty disclaimers for TI products. Unless TI explicitly designates a product as custom or customer-specified, TI products are standard, catalog, general purpose devices.

TI objects to and rejects any additional or different terms you may propose.

Copyright © 2026, Texas Instruments Incorporated

Last updated 10/2025